

# 2SK1337 Silicon N Channel MOS FET

REJ03G0934-0200 (Previous: ADE-208-1274) Rev.2.00 Sep 07, 2005

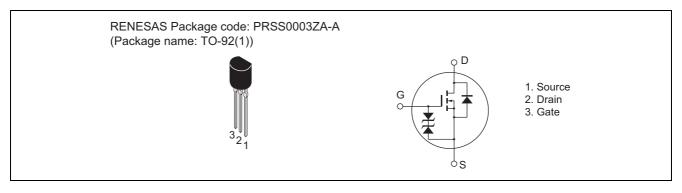
## Application

High speed power switching

### Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device
- Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

### Outline





# Absolute Maximum Ratings

			(1a - 25)C
ltem	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	100	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	ID	0.3	А
Drain peak current	I <sub>D(pulse)</sub> *1	1.2	А
Body to drain diode reverse drain current	I <sub>DR</sub>	0.3	А
Channel dissipation	Pch	400	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

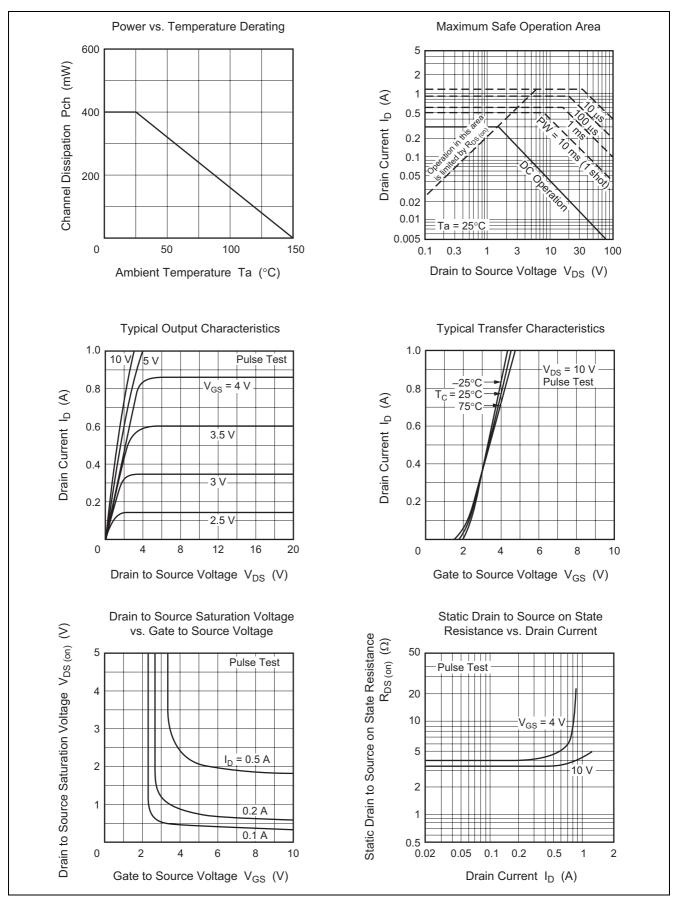
### **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	100	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	V <sub>(BR)GSS</sub>	±20	_	—	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 16 \text{ V}, \text{ V}_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	50	μA	$V_{DS} = 80 V, V_{GS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	1.0	_	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state	R <sub>DS(on)</sub>	_	3.5	4.5	Ω	$I_D = 0.2 \text{ A}, V_{GS} = 10 \text{ V}^{*2}$
resistance		_	4.0	6.5	Ω	$I_D = 0.2 \text{ A}, V_{GS} = 4 \text{ V}^{*2}$
Forward transfer admittance	y <sub>fs</sub>	0.22	0.35	—	S	$I_D = 0.2 \text{ A}, V_{DS} = 10 \text{ V}^{*2}$
Input capacitance	Ciss	_	35	—	pF	$V_{DS} = 10 V, V_{GS} = 0,$
Output capacitance	Coss	_	14	—	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	3.5	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	2	—	ns	$I_D = 0.2 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	tr	_	4		ns	R <sub>L</sub> = 150 Ω
Turn-off delay time	t <sub>d(off)</sub>	_	17	_	ns	
Fall time	t <sub>f</sub>	_	15	_	ns	
Body to drain diode forward voltage	$V_{DF}$		0.9	—	V	$I_F = 0.3 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery	t <sub>rr</sub>		80	—	ns	$I_F = 0.3 \text{ A}, V_{GS} = 0,$
time						di <sub>F</sub> /dt = 50 A/µs

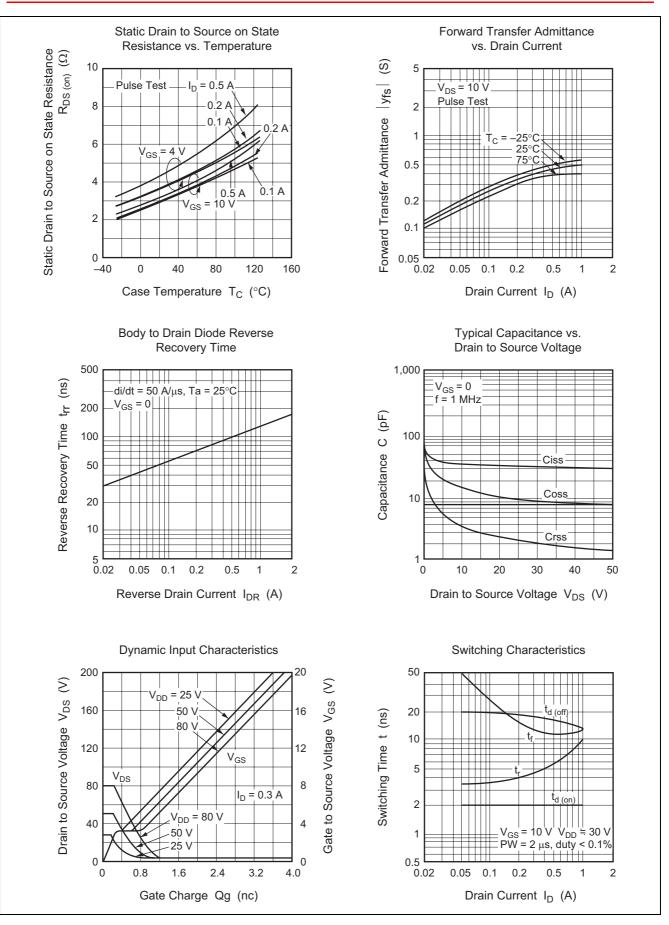
Note: 2. Pulse test



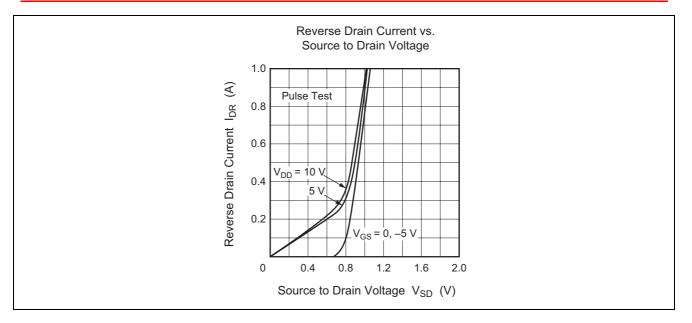
### **Main Characteristics**





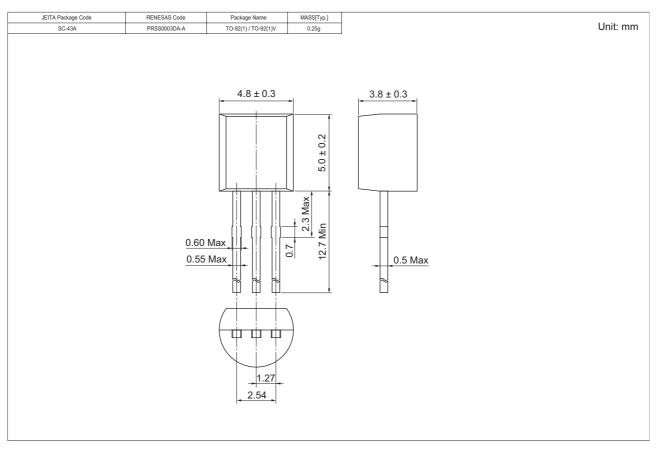








# Package Dimensions



### **Ordering Information**

Part Name	Quantity	Shipping Container
2SK1337TZ-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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